CLAIM AMENDMENTS

1. (WITHDRAWN): A stacked pad for processing substrates for the fabrication of electronic devices, the stacked pad comprising a top pad having a Shore D hardness greater than or equal to about 40 and a subpad having a Shore D hardness substantially equal to the hardness of the top pad.

2. (WITHDRAWN): The stacked pad of claim 1, wherein the top pad has a Shore D hardness from about 40 to about 70 and all ranges and values subsumed therein.

3. (WITHDRAWN): The stacked pad of claim 1, wherein the top pad has a Shore D hardness from about 50 to about 60 and all ranges and values subsumed therein.

4. (WITHDRAWN): A stacked pad for processing substrates for the fabrication of electronic devices, the stacked pad comprising a top pad having a Shore D hardness from about 40 to about 70, a subpad having a Shore D hardness equal to the hardness of the top pad, and an adhesive sandwiched between the top pad and the subpad to bind the top pad to the subpad.

5. (CURRENTLY AMENDED): A method of chemical mechanical polishing <u>and/or planarization</u>, the method comprising ~~the steps of~~:

A. providing a substrate having a surface for fabricating electronic devices, the surface comprising a dielectric material having a dielectric constant less than two;

B. providing a stacked pad, the stacked pad comprising a top pad having a Shore D hardness from about 40 to about 70 and a subpad having a Shore D hardness substantially equal to the hardness of the top pad; and

C. contacting the top pad with the surface and planarizing the surface with the stacked pad.

6. (CURRENTLY AMENDED): The method of claim 5 further comprising ~~the step of~~ conditioning the top pad using a down force less than about 0.24 psi (1.7 KPa).

7. (CURRENTLY AMENDED): The method of claim 5 further comprising ~~the step of~~ conditioning the top pad after planarization of a plurality of the substrates and performing the conditioning using a down force less than about 0.24 psi (1.7 KPa).

8. (CURRENTLY AMENDED): The method of claim 5 further comprising ~~the step of~~ planarization of five of the substrates before conditioning the top pad and performing the conditioning using a down force less than about 0.24 psi (1.7 KPa).

9. (CURRENTLY AMENDED): The method of claim 5 further comprising ~~the step of~~ repeating step A through step C a plurality of times before conditioning the top pad.

10. (CURRENTLY AMENDED): The method of claim 5 further comprising ~~the step of~~ repeating step A through step C a plurality of times before conditioning the top pad using a down force less than about 0.24 psi (1.7 KPa).

11. (ORIGINAL): The method of claim 5 further comprising conditioning the top pad only prior to the first planarization and using the stacked pad for planarizing a multiplicity of the substrates.

12. (ORIGINAL): The method of claim 5 further comprising processing a plurality of wafers between pad conditionings.

13. (ORIGINAL): The method of claim 5, wherein the stacked pad is conditioned before the first planarization.

14. (ORIGINAL): The method of claim 5, wherein the stacked pad is conditioned on a tool other than a polishing tool before the first planarization.

15. (CURRENTLY AMENDED): A method of chemical mechanical polishing and/or planarization, the method comprising ~~the steps of~~:

A. providing a substrate having a surface for fabricating electronic devices;

B. providing a stacked pad, the stacked pad comprising a top pad and a subpad, wherein the hardness or modulus of the top pad substantially equals the hardness or modulus of the subpad; and

C. contacting the top pad with the surface and planarizing the surface with the stacked pad.

16. (ORIGINAL): The method of claim 15, wherein the top pad and subpad have a compressibility of about 1.8%.

17. (ORIGINAL): The method of claim 15, wherein the top pad and subpad have a substantially equal density and the density is in the range from about 0.5 to about 0.7 grams/cc.

18. (ORIGINAL): The method of claim 15, wherein the top pad and subpad have a substantially equal pore size range and the pore size range is in the range from about 0.5 to about 0.7 grams/cc.

19. (ORIGINAL): The method of claim 15, wherein the top pad and subpad have a substantially equal density and the density is in the range from about 0.5 to about 0.7 grams/cc and the top pad and sub pad have substantially equal hardness and the Shore D hardness is greater than about 47.

20. (WITHDRAWN): A stacked pad for processing substrates for the fabrication of electronic devices, the stacked pad comprising a polyurethane impregnated felt top pad having Shore D hardness from about 51 to about 54, a polyurethane impregnated felt subpad having Shore D hardness equal to the hardness of the top pad, and an adhesive sandwiched between the top pad and the subpad to bind the top pad to the subpad; the top pad and the subpad having density of 0.58 +/- 0.04, a fiber to polymer resin ratio of 55:45, a felt density of 0.32 grams/cc, and a compressibility of 1.8%, wherein the properties of the top pad are substantially uniform and the properties of the sub pad are substantially uniform.